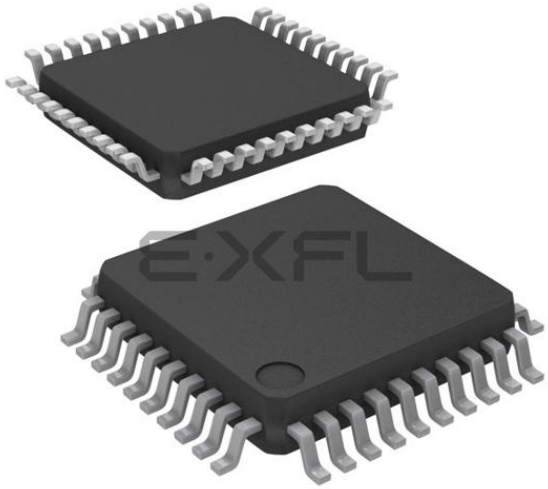
Renesas Electronics America Inc - R5F212F2DFP#W4 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	LINbus, SIO, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f212f2dfp-w4

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1.1.2 Specifications

Tables 1.1 and 1.2 outlines the Specifications for R8C/2E Group and Tables 1.3 and 1.4 outlines the Specifications for R8C/2F Group.

Table 1.1 Specifications for R8C/2E Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C/Tiny series core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM	Refer to **Table 1.5 Product List for R8C/2E Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 2
I/O Ports	Programmable I/O ports	• Input-only: 3 pins • CMOS I/O ports: 25, selectable pull-up resistor • High current drive ports: 8
Clock	Clock generation circuits	2 circuits: XIN clock oscillation circuit (with on-chip feedback resistor), On-chip oscillator (high-speed, low-speed) (high-speed on-chip oscillator has a frequency adjustment function) • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (high-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
Interrupts		• External: 4 sources, Internal: 13 sources, Software: 4 sources • Priority levels: 7 levels
Watchdog Timer		15 bits × 1 (with prescaler), reset start selectable
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
	Timer RE	8 bits × 1 Output compare mode
Serial Interface	UART0	Clock synchronous serial I/O/UART × 1
LIN Module		Hardware LIN: 1 (timer RA, UART0)
A/D Converter		10-bit resolution × 12 channels, includes sample and hold function
D/A Converter		8-bit resolution × 2 circuits
Comparator		2 circuits

Table 1.2 Specifications for R8C/2E Group (2)

Item	Specification
Flash Memory	• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 100 times • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function
Operating Frequency/Supply Voltage	f(XIN) = 20 MHz (VCC = 3.0 to 5.5 V), f(XIN) = 10 MHz (VCC = 2.7 to 5.5 V)
Current consumption	Typ. 10 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 6 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 23 μA (VCC = 3.0 V, wait mode (peripheral clock off)) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Operating Ambient Temperature	-20 to 85°C (N version) -40 to 85°C (D version)(1)
Package	32-pin LQFP Package code: PLQP0032GB-A (previous code: 32P6U-A)

NOTE:
1. Specify the D version if D version functions are to be used.

1.2 Product List

Table 1.5 lists Product List for R8C/2E Group, Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/2E Group, Table 1.6 lists Product List for R8C/2F Group, and Figure 1.2 shows a Part Number, Memory Size, and Package of R8C/2F Group.

Table 1.5 Product List for R8C/2E Group **Current of Dec. 2007**

Part No.	ROM Capacity	RAM Capacity	Package Type	Remarks
R5F212E2NFP	8 Kbytes	512 bytes	PLQP0032GB-A	N version
R5F212E4NFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	
R5F212E2DFP	8 Kbytes	512 bytes	PLQP0032GB-A	D version
R5F212E4DFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	
R5F212E2NXXXFP	8 Kbytes	512 bytes	PLQP0032GB-A	N version Factory programming product(1)
R5F212E4NXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	
R5F212E2DXXXFP	8 Kbytes	512 bytes	PLQP0032GB-A	D version Factory programming product(1)
R5F212E4DXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	

NOTE:
1. The user ROM is programmed before shipment.

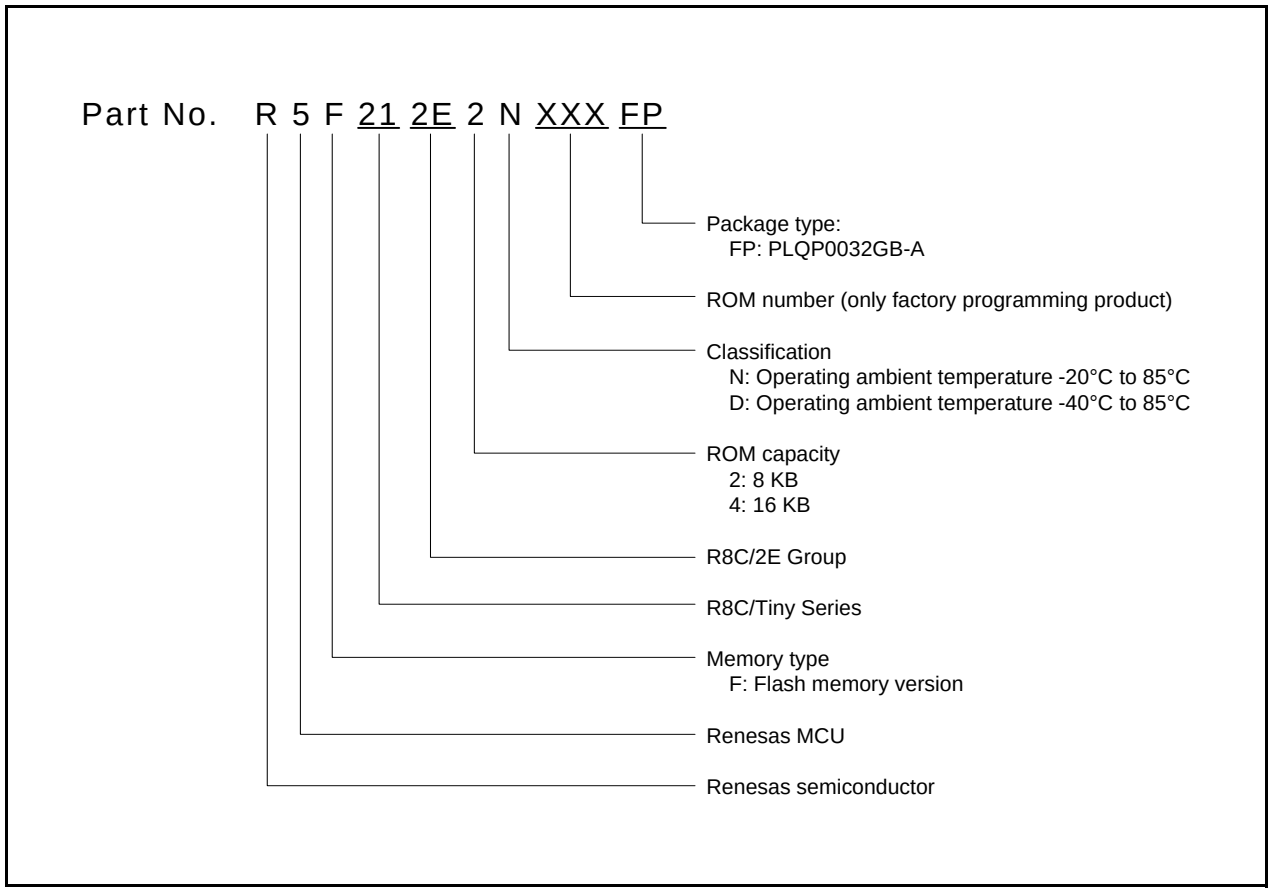
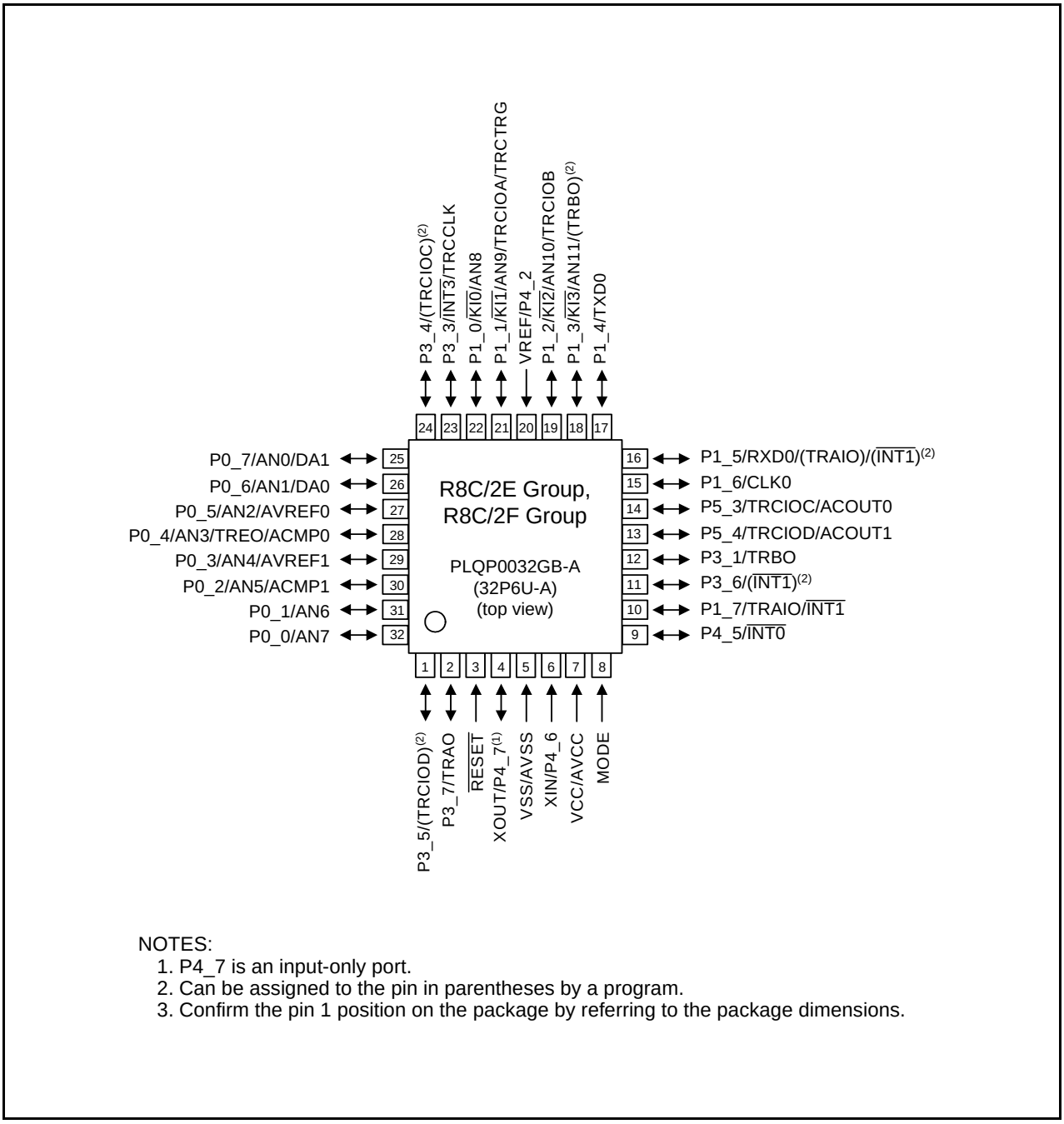


Figure 1.1 Part Number, Memory Size, and Package of R8C/2E Group

1.4 Pin Assignment

Figure 1.4 shows Pin Assignments (Top View). Table 1.7 outlines the Pin Name Information by Pin Number.



NOTES:
1. P4_7 is an input-only port.
2. Can be assigned to the pin in parentheses by a program.
3. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.4 Pin Assignments (Top View)

Table 1.7 Pin Name Information by Pin Number

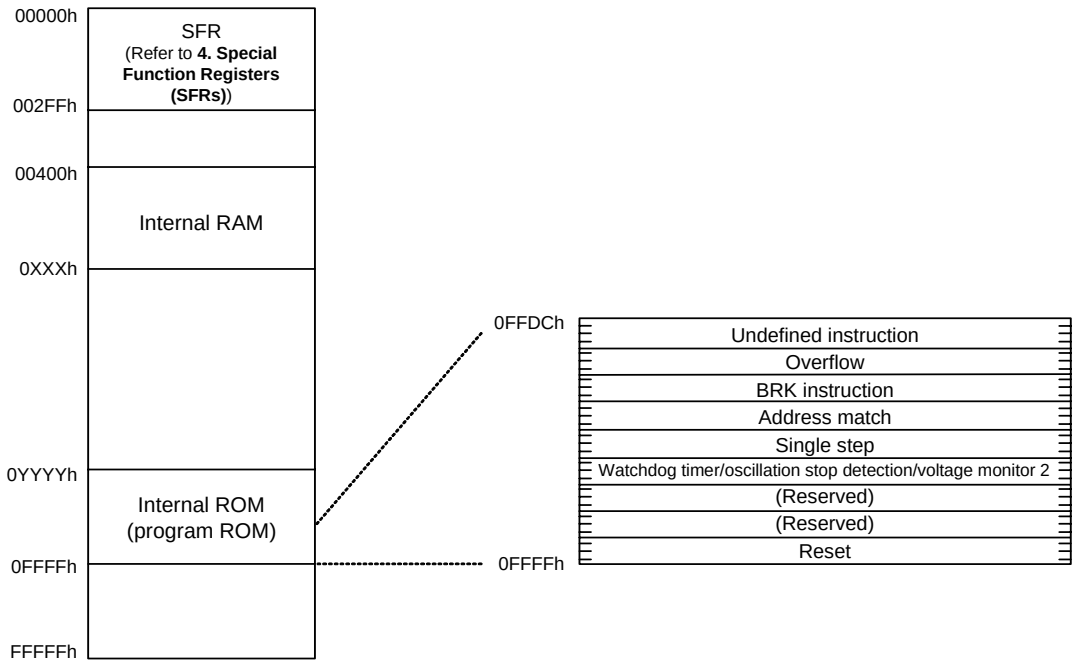
Pin Number	Control Pin	Port	I/O Pin Functions for of Peripheral Modules					
			Interrupt	Timer	Serial Interface	A/D Converter	D/A Converter	Comparator
1		P3_5		(TRCIOD)(1)				
2		P3_7		TRAO				
3	$\overline{\text{RESET}}$							
4	XOUT	P4_7						
5	VSS/AVSS							
6	XIN	P4_6						
7	VCC/AVCC							
8	MODE							
9		P4_5	$\overline{\text{INT0}}$					
10		P1_7	$\overline{\text{INT1}}$	TRAIO				
11		P3_6	($\overline{\text{INT1}}$)(1)					
12		P3_1		TRBO				
13		P5_4		TRCIOD				ACOUT1
14		P5_3		TRCIOC				ACOUT0
15		P1_6			CLK0			
16		P1_5	($\overline{\text{INT1}}$)(1)	(TRAIO)(1)	RXD0			
17		P1_4			TXD0			
18		P1_3	$\overline{\text{KI3}}$	(TRBO)(1)		AN11		
19		P1_2	$\overline{\text{KI2}}$	TRCIOB		AN10		
20	VREF	P4_2						
21		P1_1	$\overline{\text{KI1}}$	TRCIOA/ TRCTRG		AN9		
22		P1_0	$\overline{\text{KI0}}$			AN8		
23		P3_3	$\overline{\text{INT3}}$	TRCCLK				
24		P3_4		(TRCIOC)(1)				
25		P0_7				AN0	DA1	
26		P0_6				AN1	DA0	
27		P0_5				AN2		AVREF0
28		P0_4		TREO		AN3		ACMP0
29		P0_3				AN4		AVREF1
30		P0_2				AN5		ACMP1
31		P0_1				AN6		
32		P0_0				AN7		

NOTE:
1. Can be assigned to the pin in parentheses by a program.

3. Memory

3.1 R8C/2E Group

Figure 3.1 is a Memory Map of R8C/2E Group. The R8C/2E group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



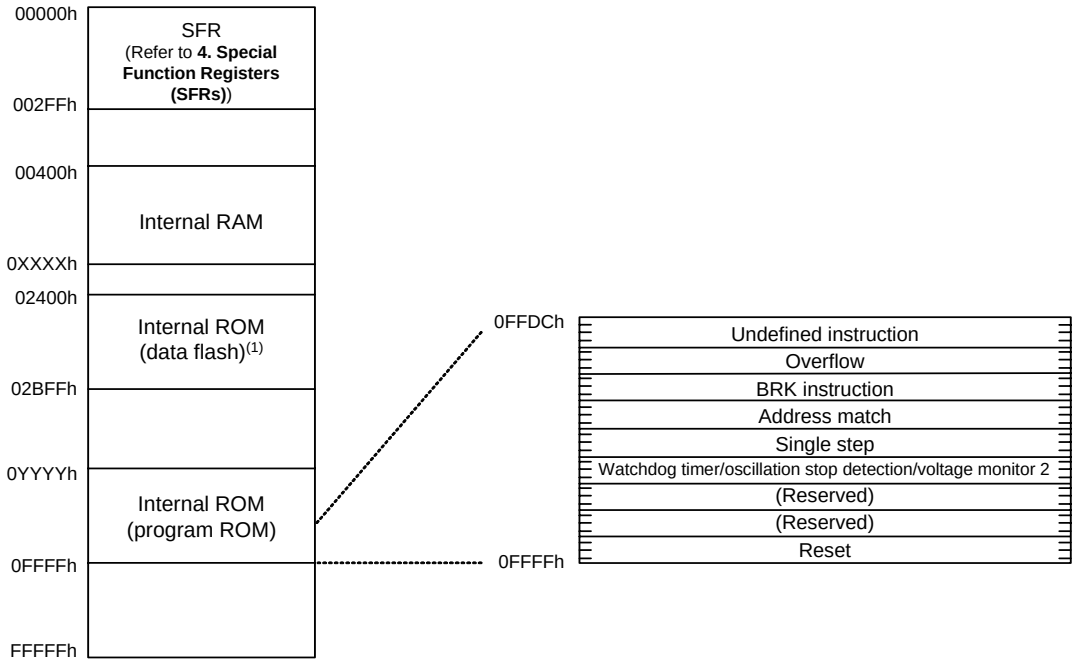
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F212E2NFP, R5F212E2DFP, R5F212E2NXXXFP, R5F212E2DXXXFP	8 Kbytes	0E000h	512 bytes	005FFh
R5F212E4NFP, R5F212E4DFP, R5F212E4NXXXFP, R5F212E4DXXXFP	16 Kbytes	0C000h	1 Kbyte	007FFh

Figure 3.1 Memory Map of R8C/2E Group

3.2 R8C/2F Group

Figure 3.2 is a Memory Map of R8C/2F Group. The R8C/2F group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F212F2NFP, R5F212F2DFP, R5F212F2NXXXFP, R5F212F2DXXXFP	8 Kbytes	0E000h	512 bytes	005FFh
R5F212F4NFP, R5F212F4DFP, R5F212F4NXXXFP, R5F212F4DXXXFP	16 Kbytes	0C000h	1 Kbyte	007FFh

Figure 3.2 Memory Map of R8C/2F Group

Table 4.3 SFR Information (3)(1)

Address	Register	Symbol	After reset
0080h			
0081h			
0082h			
0083h			
0084h			
0085h			
0086h			
0087h			
0088h			
0089h			
008Ah			
008Bh			
008Ch			
008Dh			
008Eh			
008Fh			
0090h			
0091h			
0092h			
0093h			
0094h			
0095h			
0096h			
0097h			
0098h			
0099h			
009Ah			
009Bh			
009Ch			
009Dh			
009Eh			
009Fh			
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h			
00A9h			
00AAh			
00ABh			
00ACh			
00ADh			
00AEh			
00AFh			
00B0h			
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h			
00B9h			
00BAh			
00BBh			
00BCh			
00BDh			
00BEh			
00BFh			

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 4.6 SFR Information (6)(1)

Address	Register	Symbol	After reset
0140h			
0141h			
0142h			
0143h			
0144h			
0145h			
0146h			
0147h			
0148h			
0149h			
014Ah			
014Bh			
014Ch			
014Dh			
014Eh			
014Fh			
0150h			
0151h			
0152h			
0153h			
0154h			
0155h			
0156h			
0157h			
0158h			
0159h			
015Ah			
015Bh			
015Ch			
015Dh			
015Eh			
015Fh			
0160h			
0161h			
0162h			
0163h			
0164h			
0165h			
0166h			
0167h			
0168h			
0169h			
016Ah			
016Bh			
016Ch			
016Dh			
016Eh			
016Fh			
0170h			
0171h			
0172h			
0173h			
0174h	Comparator 0 Control Register	ACCR0	00001000b
0175h	Comparator 1 Control Register	ACCR1	00001000b
0176h			
0177h	Comparator Mode Register	ACMR	00h
0178h			
0179h			
017Ah			
017Bh			
017Ch			
017Dh			
017Eh			
017Fh			

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 4.7 SFR Information (7)[1]

Address	Register	Symbol	After reset
0180h			
0181h			
0182h			
0183h			
0184h			
0185h			
0186h			
0187h			
0188h			
0189h			
018Ah			
018Bh			
018Ch			
018Dh			
018Eh			
018Fh			
0190h			
0191h			
0192h			
0193h			
0194h			
0195h			
0196h			
0197h			
0198h			
0199h			
019Ah			
019Bh			
019Ch			
019Dh			
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h			
01B3h	Flash Memory Control Register 4	FMR4	01000000b
01B4h			
01B5h	Flash Memory Control Register1	FMR1	1000000Xb
01B6h			
01B7h	Flash Memory Control Register 0	FMR0	00000001b
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			

FFFFh	Option Function Select Register	OFS	(Note 2)

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a program. Use a flash programmer to write to it.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		–0.3 to 6.5	V
V_I	Input voltage		–0.3 to V_{CC} + 0.3	V
V_O	Output voltage		–0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	T_{opr} = 25°C	500	mW
T_{opr}	Operating ambient temperature		–20 to 85 (N version) / –40 to 85 (D version)	°C
T_{stg}	Storage temperature		–65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage			2.7	–	5.5	V
V_{SS}/AV_{SS}	Supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8 V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2 V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$		–	–	–160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$		–	–	–80	mA
$I_{OH(peak)}$	Peak output “H” current	Except P1_0 to P1_7		–	–	–10	mA
		P1_0 to P1_7		–	–	–20	mA
$I_{OH(avg)}$	Average output “H” current	Except P1_0 to P1_7		–	–	–5	mA
		P1_0 to P1_7		–	–	–10	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins $I_{OL(peak)}$		–	–	160	mA
$I_{OL(sum)}$	Average sum output “L” currents	Sum of all pins $I_{OL(avg)}$		–	–	80	mA
$I_{OL(peak)}$	Peak output “L” currents	Except P1_0 to P1_7		–	–	10	mA
		P1_0 to P1_7		–	–	20	mA
$I_{OL(avg)}$	Average output “L” current	Except P1_0 to P1_7		–	–	5	mA
		P1_0 to P1_7		–	–	10	mA
$f_{(XIN)}$	XIN clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V	0	–	20	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
–	System clock	OCD2 = 0 XIN clock selected	3.0 V ≤ V_{CC} ≤ 5.5 V	0	–	20	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
		OCD2 = 1 On-chip oscillator clock selected	FRA01 = 0 Low-speed on-chip oscillator clock selected	–	125	–	kHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 3.0 V ≤ V_{CC} ≤ 5.5 V	–	–	20	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	10	MHz

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

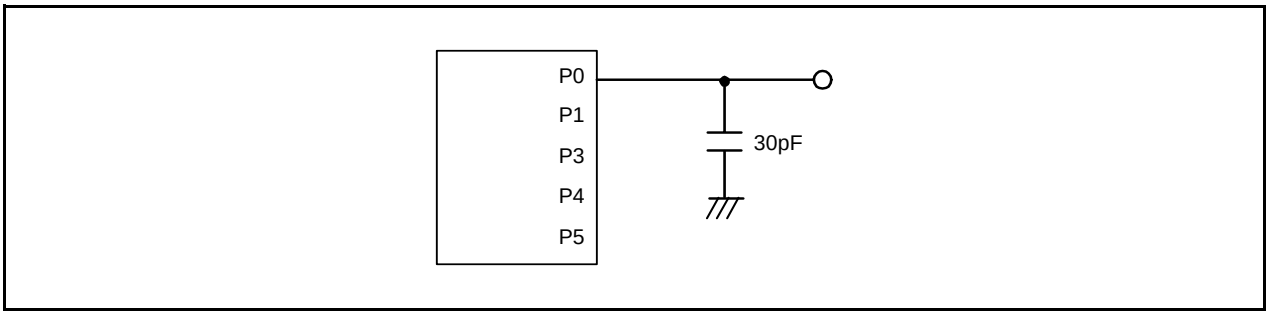


Figure 5.1 Ports P0, P1, and P3 to P5 Timing Measurement Circuit

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}	–	–	10	Bits
–	Absolute accuracy	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±3	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±2	LSB
		10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±5	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±2	LSB
R_{ladder}	Resistor ladder		V_{ref} = AV_{CC}	10	–	40	kΩ
t_{conv}	Conversion time	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	3.3	–	–	µs
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	2.8	–	–	µs
V_{ref}	Reference voltage			2.7	–	AV_{CC}	V
V_{IA}	Analog input voltage(2)			0	–	AV_{CC}	V
–	A/D operating clock frequency	Without sample and hold	V_{ref} = AV_{CC} = 2.7 to 5.5 V	0.25	–	10	MHz
		With sample and hold	V_{ref} = AV_{CC} = 2.7 to 5.5 V	1	–	10	MHz

NOTES:
1. AV_{CC} = 2.7 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.4 D/A Converter Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Resolution		–	–	8	Bit
–	Absolute accuracy		–	–	1.0	%
t_{su}	Setup time		–	–	3	µs
R_O	Output resistor		4	10	20	kΩ
I_{Vref}	Reference power input current	(NOTE 2)	–	–	1.5	mA

NOTES:
1. AV_{CC} = 2.7 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. This applies when one D/A converter is used and the value of the DAi register (i = 0 or 1) for the unused D/A converter is 00h. The resistor ladder of the A/D converter is not included. Also, even if the VCUT bit in the ADCON1 register is set to 0 (V_{REF} not connected), I_{Vref} flows into the D/A converters.

Table 5.7 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		–20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. –40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.11 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	V_{CC} = 4.75 V to 5.25 V 0°C ≤ T_{opr} ≤ 60°C(2)	39.2	40	40.8	MHz
		V_{CC} = 3.0 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C(2)	38.8	40	41.2	MHz
		V_{CC} = 3.0 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C(2)	38.4	40	41.6	MHz
		V_{CC} = 2.7 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C(2)	38	40	42	MHz
		V_{CC} = 2.7 V to 5.5 V –40°C ≤ T_{opr} ≤ 85°C(2)	37.6	40	42.4	MHz
		V_{CC} = 5.0 V ±10% –20°C ≤ T_{opr} ≤ 85°C(2)	38.8	40	40.8	MHz
		V_{CC} = 5.0 V ±10% –40°C ≤ T_{opr} ≤ 85°C(2)	38.4	40	40.8	MHz
	High-speed on-chip oscillator frequency when correction value in FRA7 register is written to FRA1 register	V_{CC} = 5.0 V, T_{opr} = 25°C	–	36.864	–	MHz
		V_{CC} = 2.7 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	–3%	–	3%	%
–	Value in FRA1 register after reset		08h	–	F7h	–
–	Oscillation frequency adjustment unit of high-speed on-chip oscillator	Adjust FRA1 register (value after reset) to –1	–	+0.3	–	MHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	400	–	µA

NOTES:
1. V_{CC} = 2.7 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. These standard values show when the FRA1 register value after reset is assumed.

Table 5.12 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		30	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	15	–	µA

NOTE:
1. V_{CC} = 2.7 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Table 5.13 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until system clock supply starts after the interrupt is acknowledged to exit stop mode.

Timing Requirements
(Unless Otherwise Specified: V_{CC} = 5 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 5 V]

Table 5.16 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns

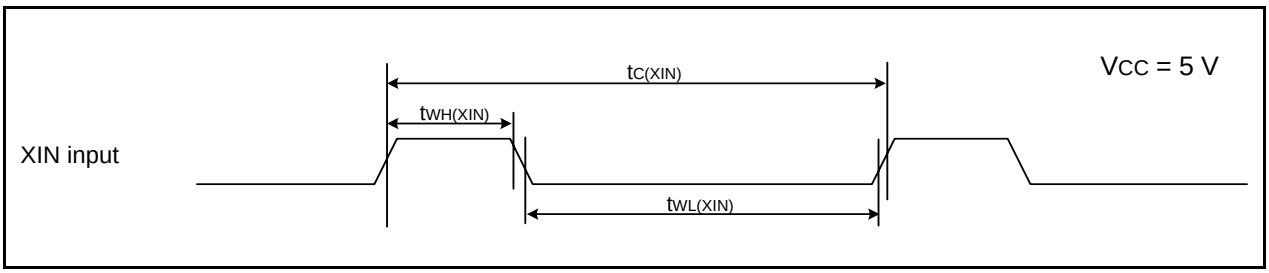


Figure 5.4 XIN Input Timing Diagram when V_{CC} = 5 V

Table 5.17 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

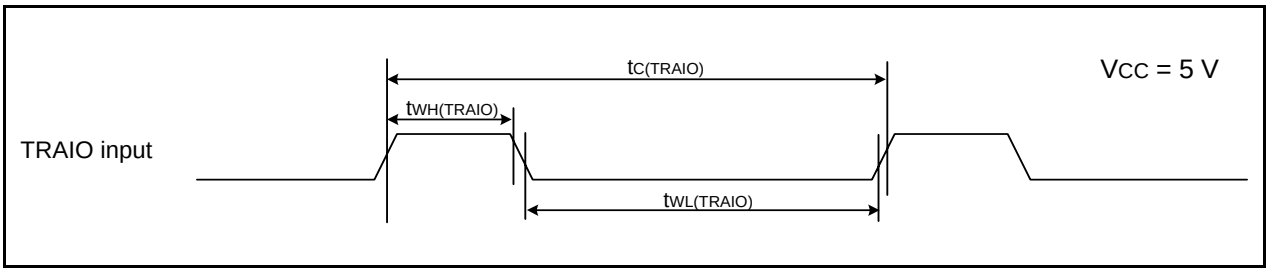


Figure 5.5 TRAIO Input Timing Diagram when V_{CC} = 5 V

Table 5.18 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLK0 input cycle time	200	–	ns
$t_{W(CKH)}$	CLK0 input “H” width	100	–	ns
$t_{W(CKL)}$	CLK0 input “L” width	100	–	ns
$t_{d(C-Q)}$	TXD0 output delay time	–	50	ns
$t_{h(C-Q)}$	TXD0 hold time	0	–	ns
$t_{su(D-C)}$	RXD0 input setup time	50	–	ns
$t_{h(C-D)}$	RXD0 input hold time	90	–	ns

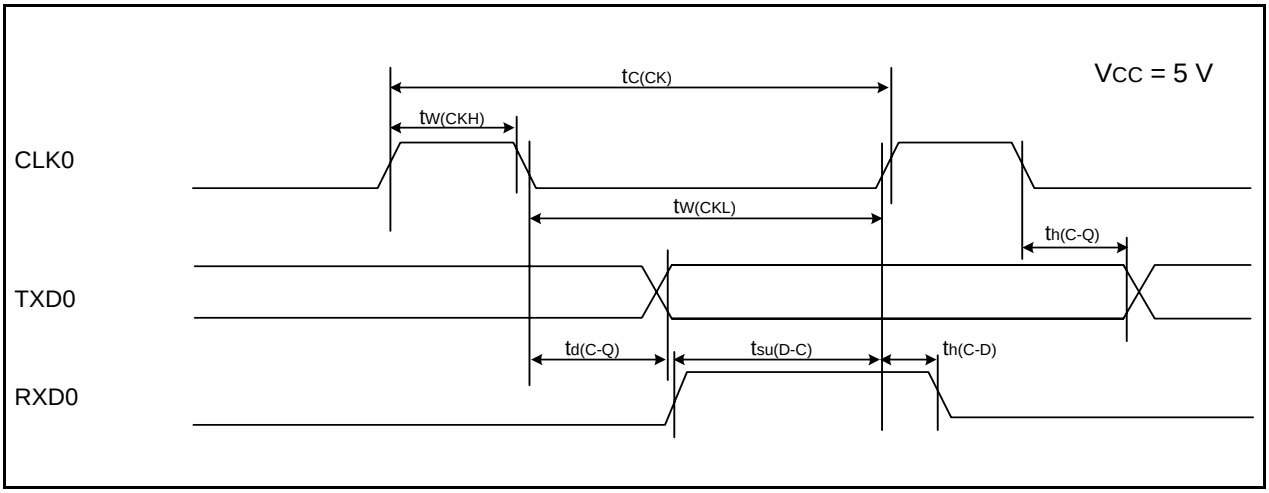


Figure 5.6 Serial Interface Timing Diagram when VCC = 5 V

Table 5.19 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width	250(1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width	250(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

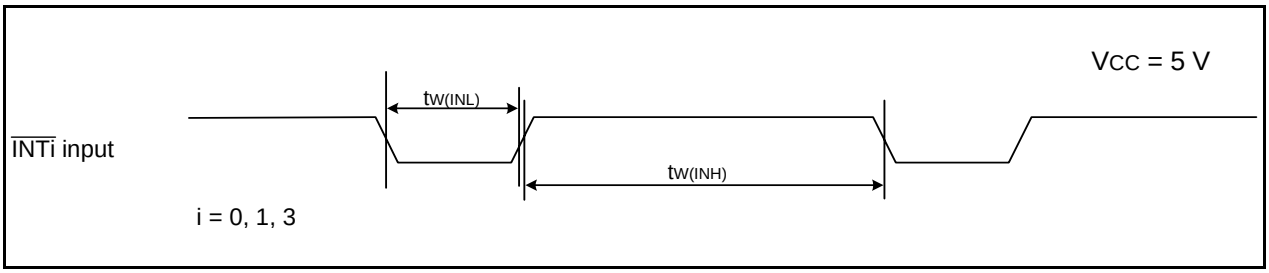


Figure 5.7 External Interrupt $\overline{INTi}$ Input Timing Diagram when VCC = 5 V

Timing requirements
(Unless Otherwise Specified: V_{CC} = 3 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 3 V]

Table 5.22 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	100	–	ns
$t_{WH(XIN)}$	XIN input “H” width	40	–	ns
$t_{WL(XIN)}$	XIN input “L” width	40	–	ns

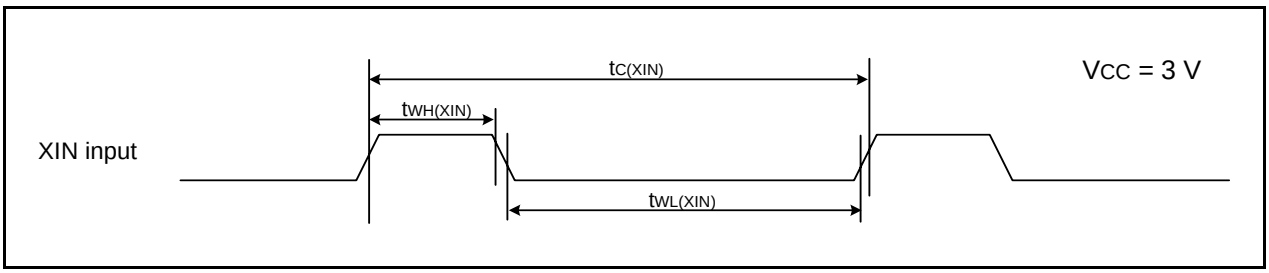


Figure 5.8 XIN Input Timing Diagram when V_{CC} = 3 V

Table 5.23 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	–	ns

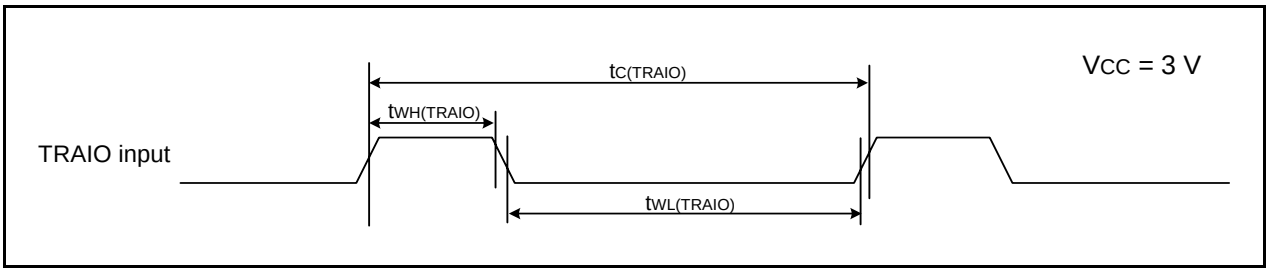


Figure 5.9 TRAIO Input Timing Diagram when V_{CC} = 3 V

REVISION HISTORY	R8C/2E Group, R8C/2F Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Aug 01, 2007	–	First Edition issued
1.00	Dec 14, 2007	All pages	“Under development” deleted
		2, 4	Table 1.1, Table 1.3: “Interrupts” revised
		6, 7	Table 1.5, Table 1.6: “(D)” deleted
		15, 16	Figure 3.1, Figure 3.2: “Expanded area” deleted
		17	Table 4.1: “002Ch” added
		24	Table 5.2: I_{OH}(sum), NOTE2 revised
		30	Table 5.11: Symbol “fOCO40M”; Parameter added

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